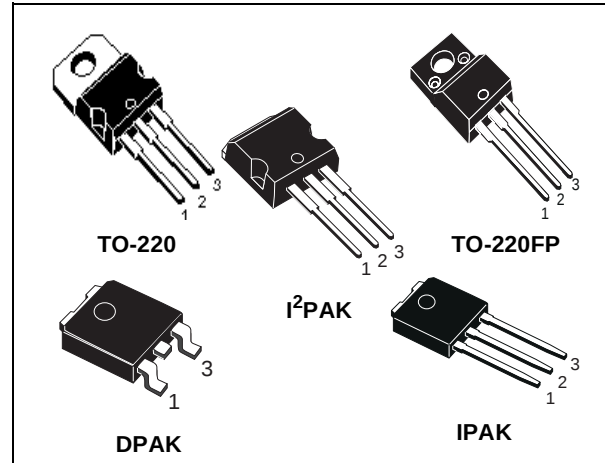


N-CHANNEL 500V-1.22 Ω -4.4A TO-220/FP/DPAK/IPAK/I²PAK Zener-Protected SuperMESH™ Power MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D	P _w
STP5NK50Z	500 V	< 1.5 Ω	4.4 A	70 W
STP5NK50ZFP	500 V	< 1.5 Ω	4.4 A	25 W
STD5NK50Z	500 V	< 1.5 Ω	4.4 A	70 W
STD5NK50Z-1	500 V	< 1.5 Ω	4.4 A	70 W
STB5BK50Z-1	500 V	< 1.5 Ω	4.4 A	70 W

- TYPICAL R_{DS(on)} = 1.22 Ω
- EXTREMELY HIGH dv/dt CAPABILITY
- 100% AVALANCHE TESTED
- GATE CHARGE MINIMIZED
- VERY LOW INTRINSIC CAPACITANCES
- VERY GOOD MANUFACTURING REPEATABILITY



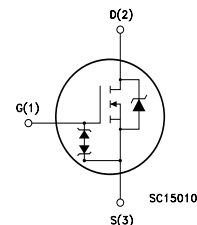
DESCRIPTION

The SuperMESH™ series is obtained through an extreme optimization of ST's well established strip-based PowerMESH™ layout. In addition to pushing on-resistance significantly down, special care is taken to ensure a very good dv/dt capability for the most demanding applications. Such series complements ST full range of high voltage MOSFETs including revolutionary MDmesh™ products.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- IDEAL FOR OFF-LINE POWER SUPPLIES, ADAPTORS AND PFC
- LIGHTING

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STP5NK50Z	P5NK50Z	TO-220	TUBE
STP5NK50ZFP	P5NK50ZFP	TO-220FP	TUBE
STD5NK50ZT4	D5NK50Z	DPAK	TAPE & REEL
STD5NK50Z-1	D5NK50Z	IPAK	TUBE
STB5NK50Z-1	B5NK50Z	I ² PAK	TUBE

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value			Unit
		STP5NK50Z STB5NK50Z-1	STP5NK50ZFP	STD5NK50Z STD5NK50Z-1	
V_{DS}	Drain-source Voltage ($V_{GS} = 0$)	500			V
V_{DGR}	Drain-gate Voltage ($R_{GS} = 20\text{ k}\Omega$)	500			V
V_{GS}	Gate- source Voltage	± 30			V
I_D	Drain Current (continuous) at $T_C = 25^\circ\text{C}$	4.4	4.4 (*)	4.4	A
I_D	Drain Current (continuous) at $T_C = 100^\circ\text{C}$	2.7	2.7 (*)	2.7	A
$I_{DM}(\bullet)$	Drain Current (pulsed)	17.6	17.6 (*)	17.6	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	70	25	70	W
	Derating Factor	0.56	0.2	0.56	W/ $^\circ\text{C}$
$V_{ESD(G-S)}$	Gate source ESD(HBM-C=100pF, R=1.5K Ω)	3000			V
$dv/dt(1)$	Peak Diode Recovery voltage slope	4.5			V/ns
V_{ISO}	Insulation Withstand Voltage (DC)	-	2500	-	V
T_j T_{stg}	Operating Junction Temperature Storage Temperature	-55 to 150 -55 to 150			$^\circ\text{C}$ $^\circ\text{C}$

(●) Pulse width limited by safe operating area

(1) $I_{SD} \leq 4.4\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq V_{(BR)DSS}$, $T_j \leq T_{JMAX}$.

(*) Limited only by maximum temperature allowed

THERMAL DATA

		TO-220 I ² PAK	TO-220FP	DPAK	
$R_{thj-case}$	Thermal Resistance Junction-case Max	1.78	5	1.78	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal Resistance Junction-ambient Max	62.5			$^\circ\text{C}/\text{W}$
T_I	Maximum Lead Temperature For Soldering Purpose	300			$^\circ\text{C}$

AVALANCHE CHARACTERISTICS

Symbol	Parameter	Max Value	Unit
I_{AR}	Avalanche Current, Repetitive or Not-Repetitive (pulse width limited by T_j max)	4.4	A
E_{AS}	Single Pulse Avalanche Energy (starting $T_j = 25^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	130	mJ

GATE-SOURCE ZENER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV_{GSO}	Gate-Source Breakdown Voltage	$I_{GS} = \pm 1\text{mA}$ (Open Drain)	30			V

ELECTRICAL CHARACTERISTICS (TCASE =25°C UNLESS OTHERWISE SPECIFIED)
ON/OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source Breakdown Voltage	$I_D = 1 \text{ mA}$, $V_{GS} = 0$	500			V
I_{DSS}	Zero Gate Voltage Drain Current ($V_{GS} = 0$)	$V_{DS} = \text{Max Rating}$ $V_{DS} = \text{Max Rating}$, $T_C = 125^\circ\text{C}$			1 50	μA μA
I_{GSS}	Gate-body Leakage Current ($V_{DS} = 0$)	$V_{GS} = \pm 20\text{V}$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}$, $I_D = 50\mu\text{A}$	3	3.75	4.5	V
$R_{DS(on)}$	Static Drain-source On Resistance	$V_{GS} = 10\text{V}$, $I_D = 2.2 \text{ A}$		1.22	1.5	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs} (1)$	Forward Transconductance	$V_{DS} = 15 \text{ V}$, $I_D = 2.2 \text{ A}$		3.1		S
C_{iss} C_{oss} C_{rss}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{DS} = 25\text{V}$, $f = 1 \text{ MHz}$, $V_{GS} = 0$		535 75 17		pF pF pF
$C_{oss \text{ eq.}} (3)$	Equivalent Output Capacitance	$V_{GS} = 0\text{V}$, $V_{DS} = 0\text{V to } 400\text{V}$		45		pF

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{DD} = 250 \text{ V}$, $I_D = 2.2 \text{ A}$ $R_G = 4.7\Omega$ $V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		15 10		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 400\text{V}$, $I_D = 4.4 \text{ A}$, $V_{GS} = 10\text{V}$		20 4 10	28	nC nC nC

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 250 \text{ V}$, $I_D = 2.2\text{A}$ $R_G = 4.7\Omega$ $V_{GS} = 10 \text{ V}$ (Resistive Load see, Figure 3)		32 15		ns ns
$t_r(V_{off})$ t_f t_c	Off-voltage Rise Time Fall Time Cross-over Time	$V_{DD} = 400\text{V}$, $I_D = 4.4\text{A}$, $R_G = 4.7\Omega$, $V_{GS} = 10\text{V}$ (Inductive Load see, Figure 5)		12 12 20		ns ns ns

SOURCE DRAIN DIODE

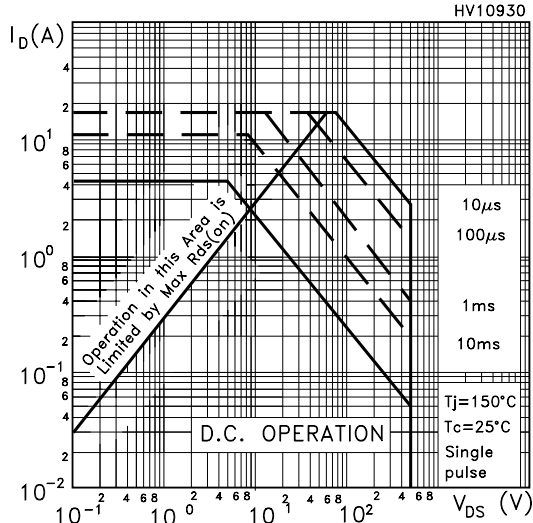
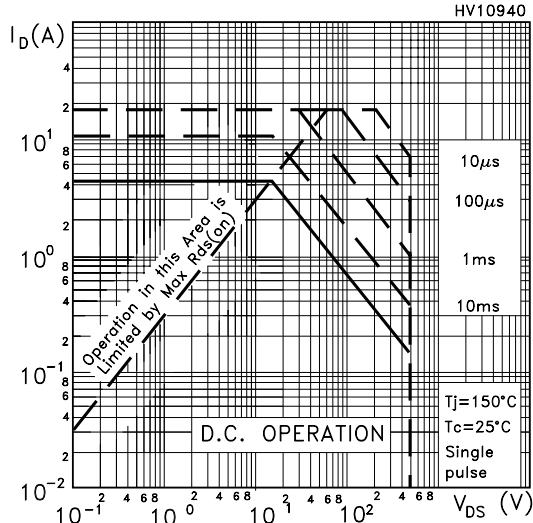
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (2)$	Source-drain Current Source-drain Current (pulsed)				4.4 17.6	A A
$V_{SD} (1)$	Forward On Voltage	$I_{SD} = 4.4 \text{ A}$, $V_{GS} = 0$			1.6	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 4.4 \text{ A}$, $di/dt = 100\text{A}/\mu\text{s}$ $V_{DD} = 30\text{V}$, $T_J = 150^\circ\text{C}$ (see test circuit, Figure 5)		310 1425 9.2		ns nC A

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

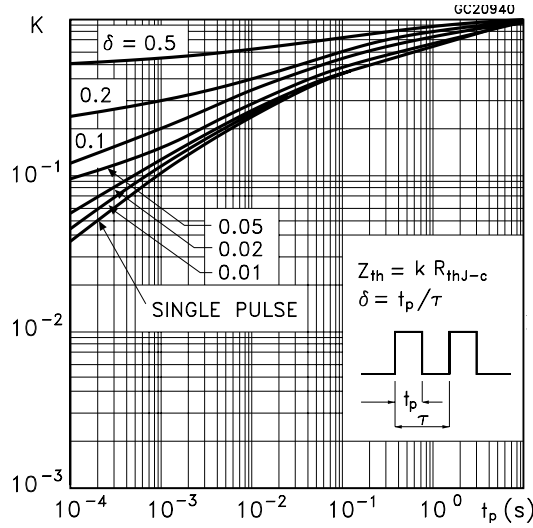
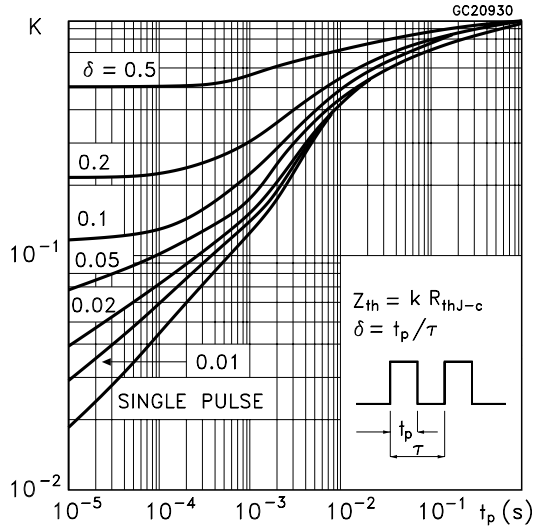
2. Pulse width limited by safe operating area.

3. $C_{oss \text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80%
V

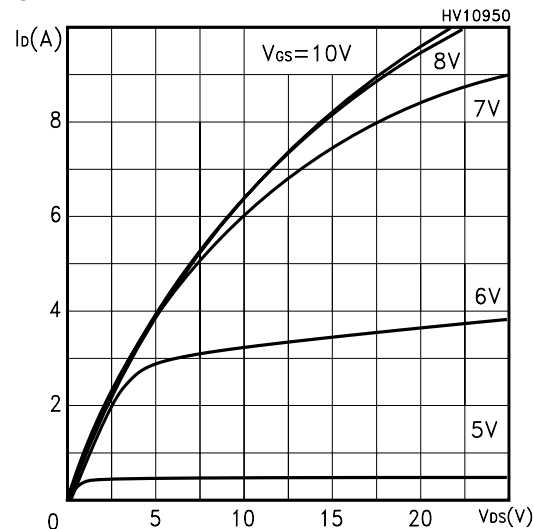
Safe Operating Area For TO-220/DPAK/IPAK/I2PAK Safe Operating Area For TO-220FP



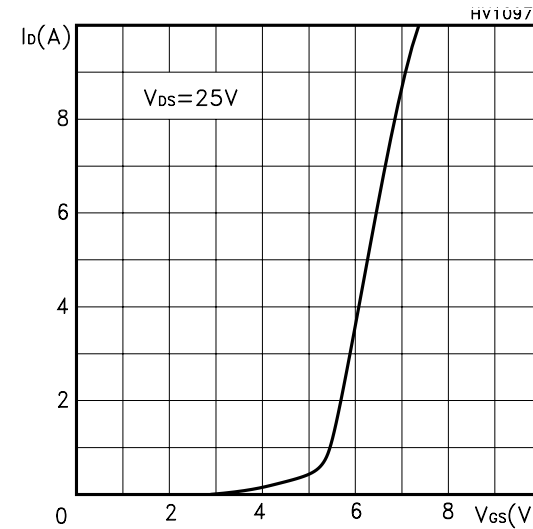
Thermal Impedance For TO-220/DPAK/IPAK/I2PAK Thermal Impedance For TO-220FP



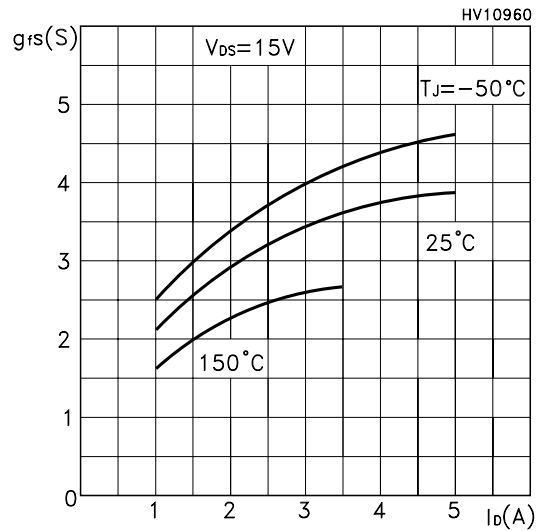
Output Characteristics



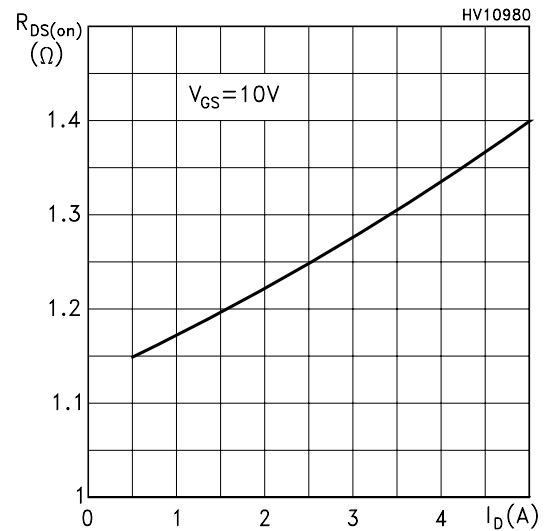
Transfer Characteristics



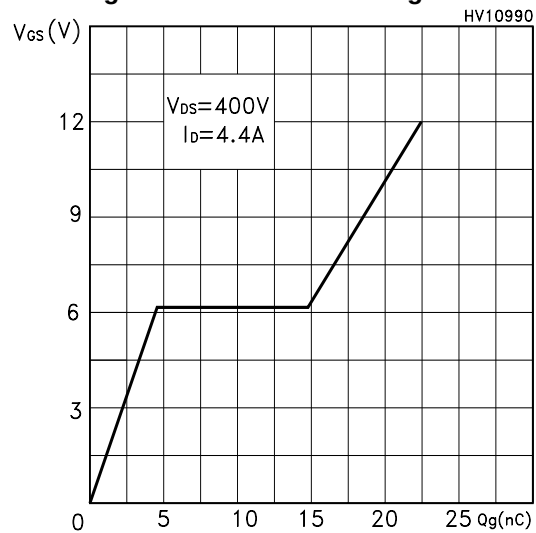
Transconductance



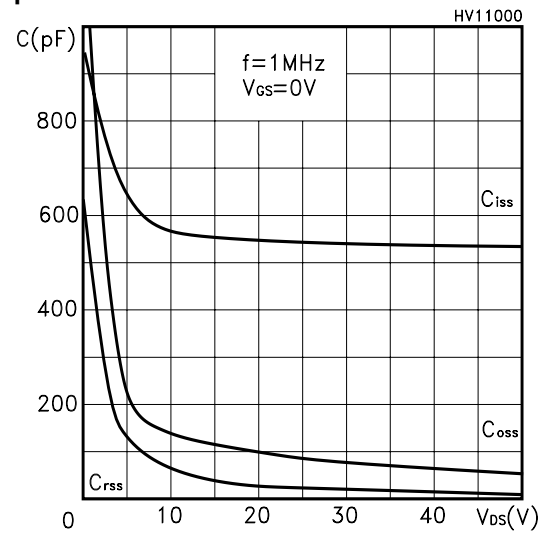
Static Drain-source On Resistance



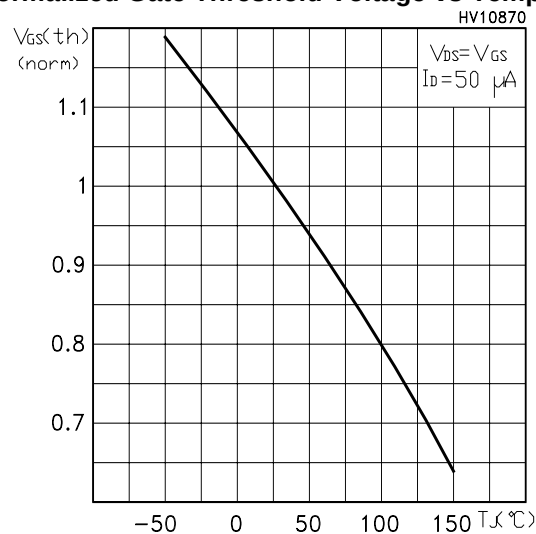
Gate Charge vs Gate-source Voltage



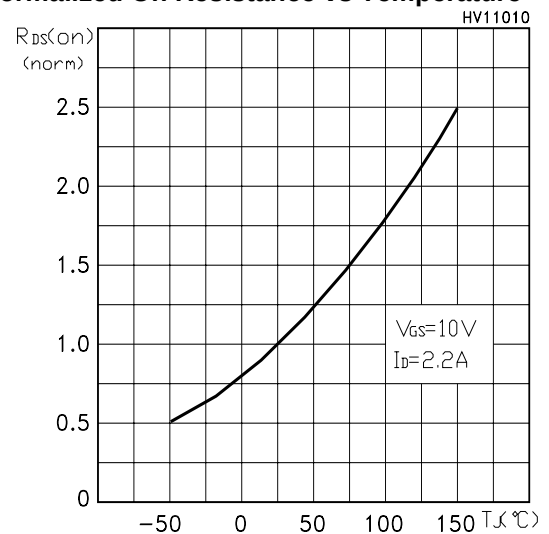
Capacitance Variations



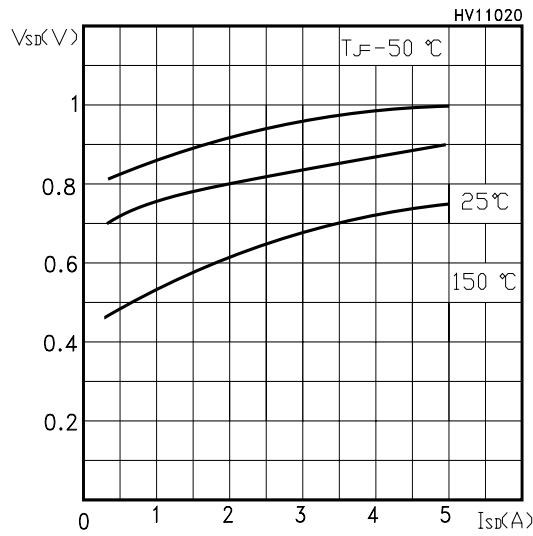
Normalized Gate Threshold Voltage vs Temp.



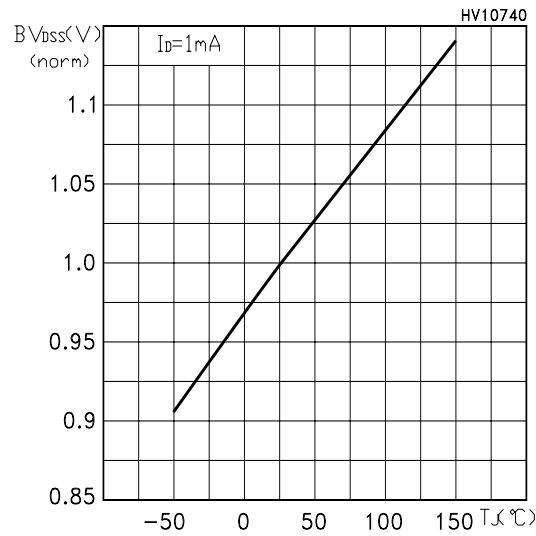
Normalized On Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized BVDSS vs Temperature



Maximum Avalanche Energy vs Temperature

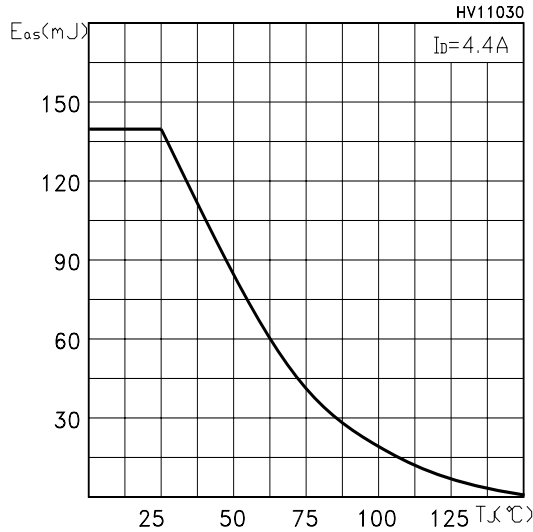


Fig. 1: Unclamped Inductive Load Test Circuit

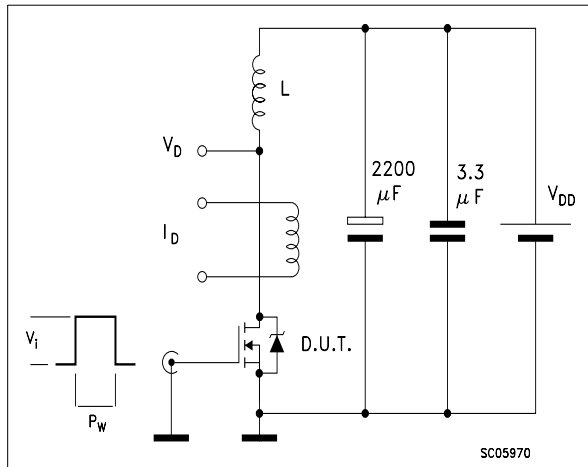


Fig. 2: Unclamped Inductive Waveform

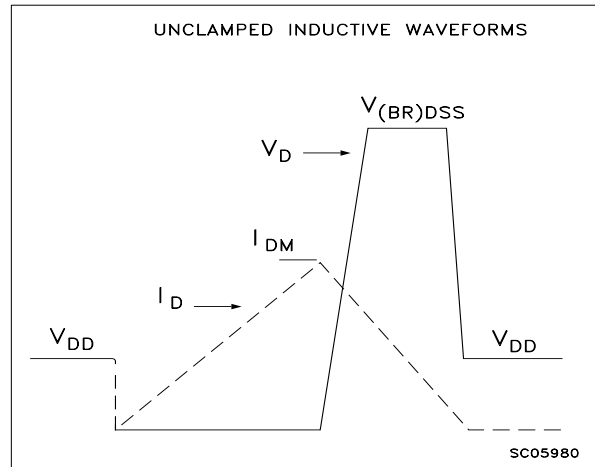


Fig. 3: Switching Times Test Circuit For Resistive Load

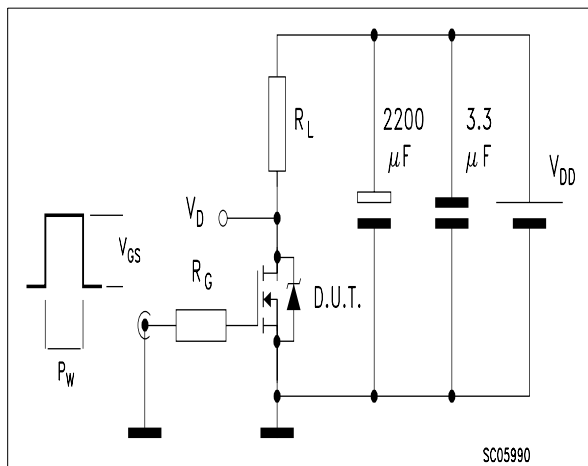


Fig. 4: Gate Charge test Circuit

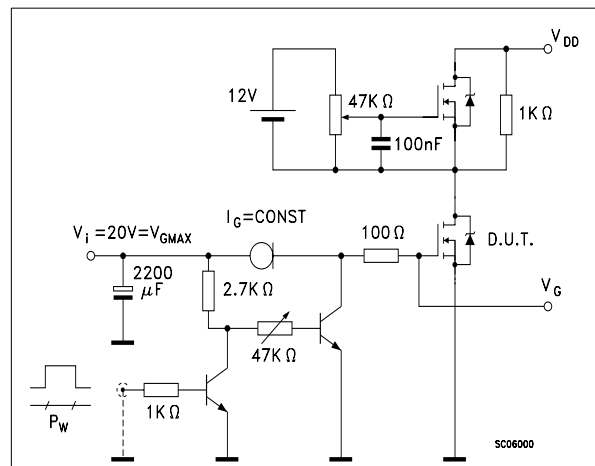
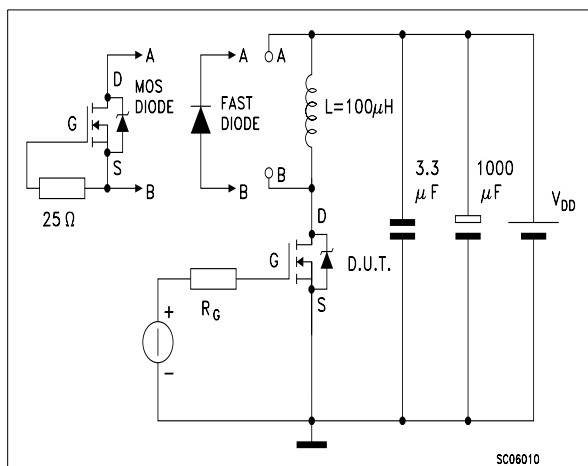
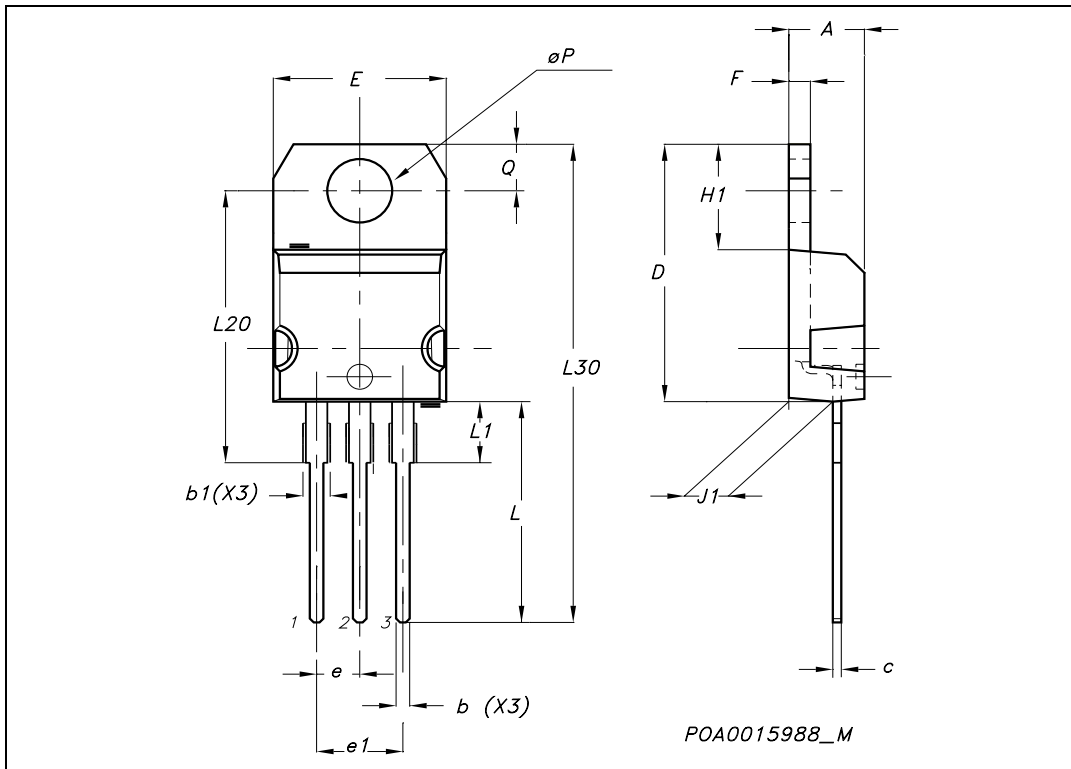


Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



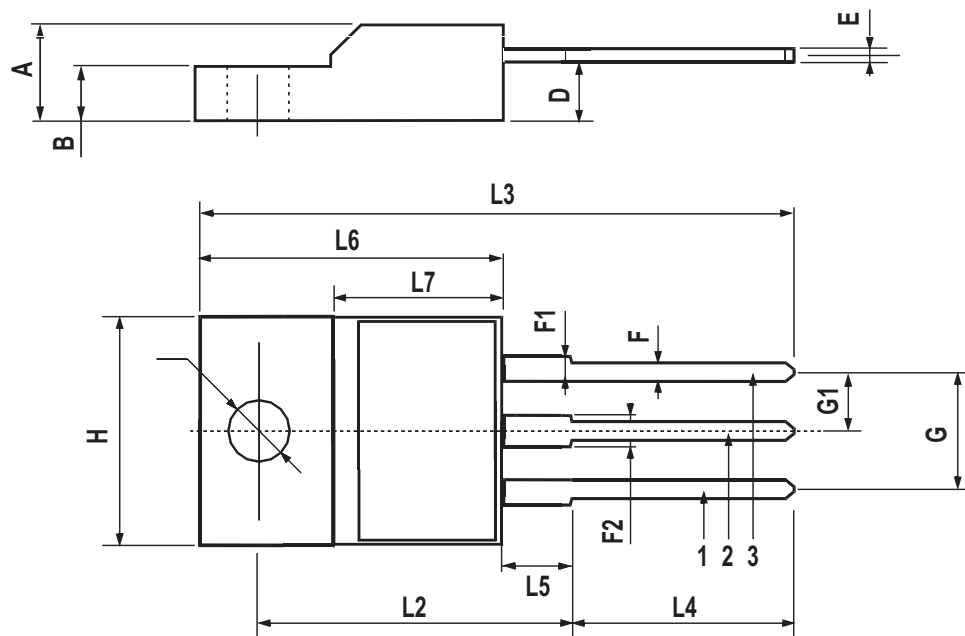
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



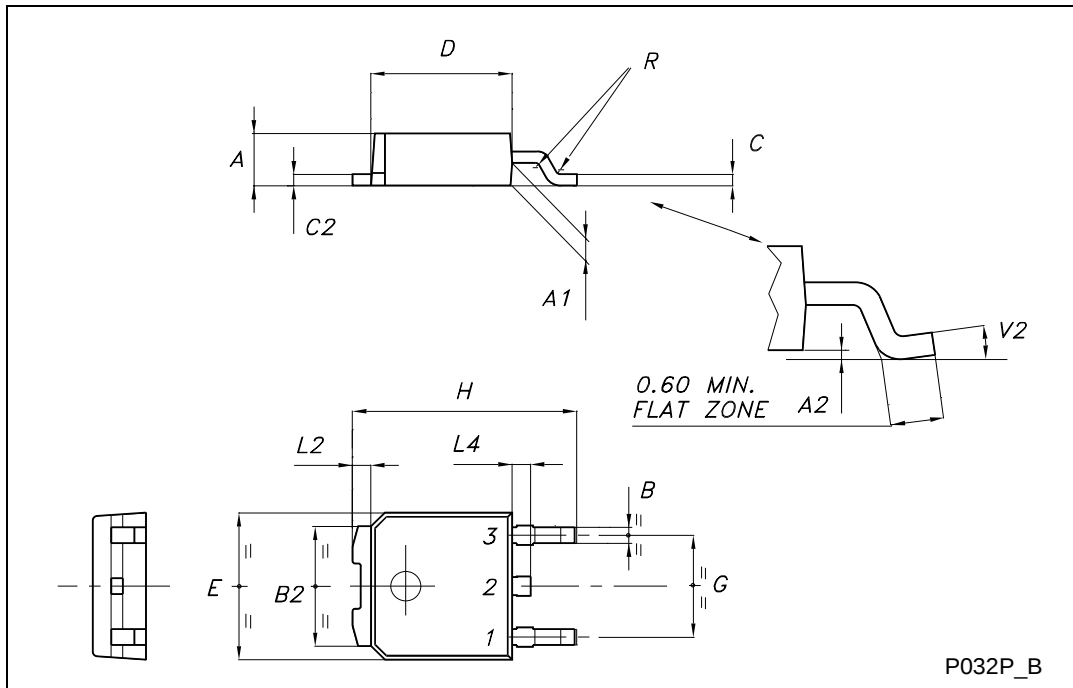
TO-220FP MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.5	0.045		0.067
F2	1.15		1.5	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



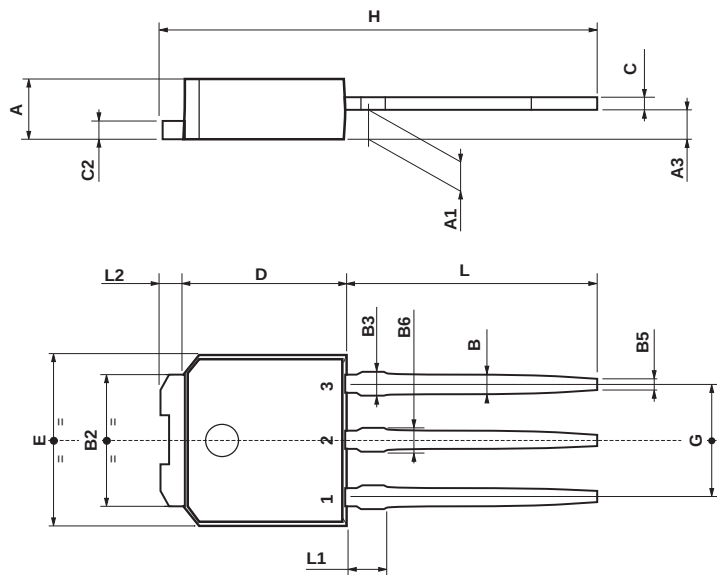
TO-252 (DPAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



TO-251 (IPAK) MECHANICAL DATA

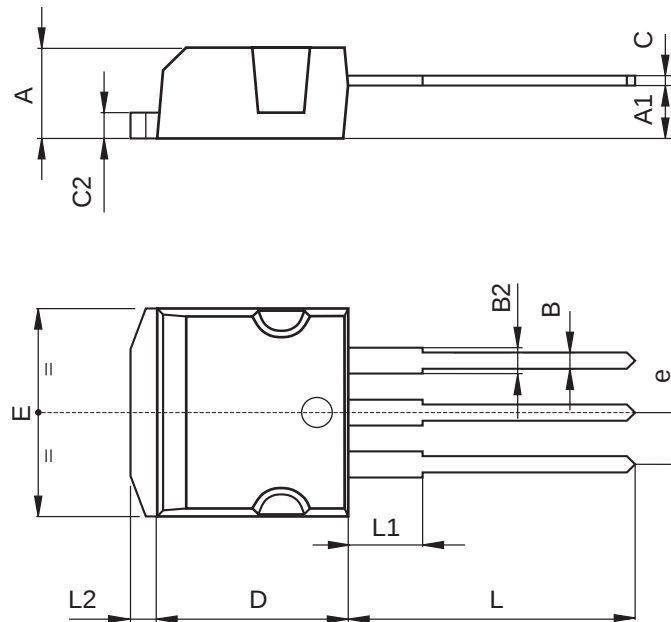
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.2		2.4	0.086		0.094
A1	0.9		1.1	0.035		0.043
A3	0.7		1.3	0.027		0.051
B	0.64		0.9	0.025		0.031
B2	5.2		5.4	0.204		0.212
B3			0.85			0.033
B5		0.3			0.012	
B6			0.95			0.037
C	0.45		0.6	0.017		0.023
C2	0.48		0.6	0.019		0.023
D	6		6.2	0.236		0.244
E	6.4		6.6	0.252		0.260
G	4.4		4.6	0.173		0.181
H	15.9		16.3	0.626		0.641
L	9		9.4	0.354		0.370
L1	0.8		1.2	0.031		0.047
L2		0.8	1		0.031	0.039



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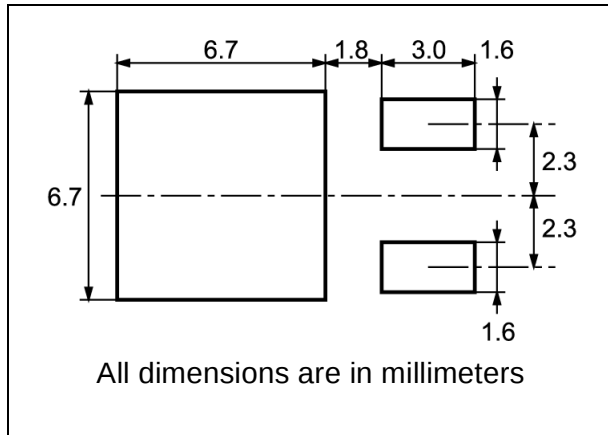
TO-262 (I²PAK) MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
e	2.4		2.7	0.094		0.106
E	10		10.4	0.393		0.409
L	13.1		13.6	0.515		0.531
L1	3.48		3.78	0.137		0.149
L2	1.27		1.4	0.050		0.055

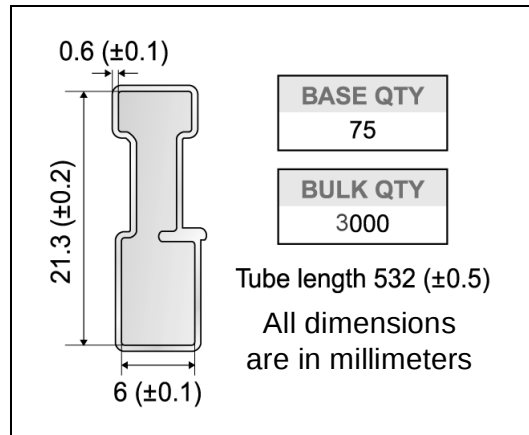


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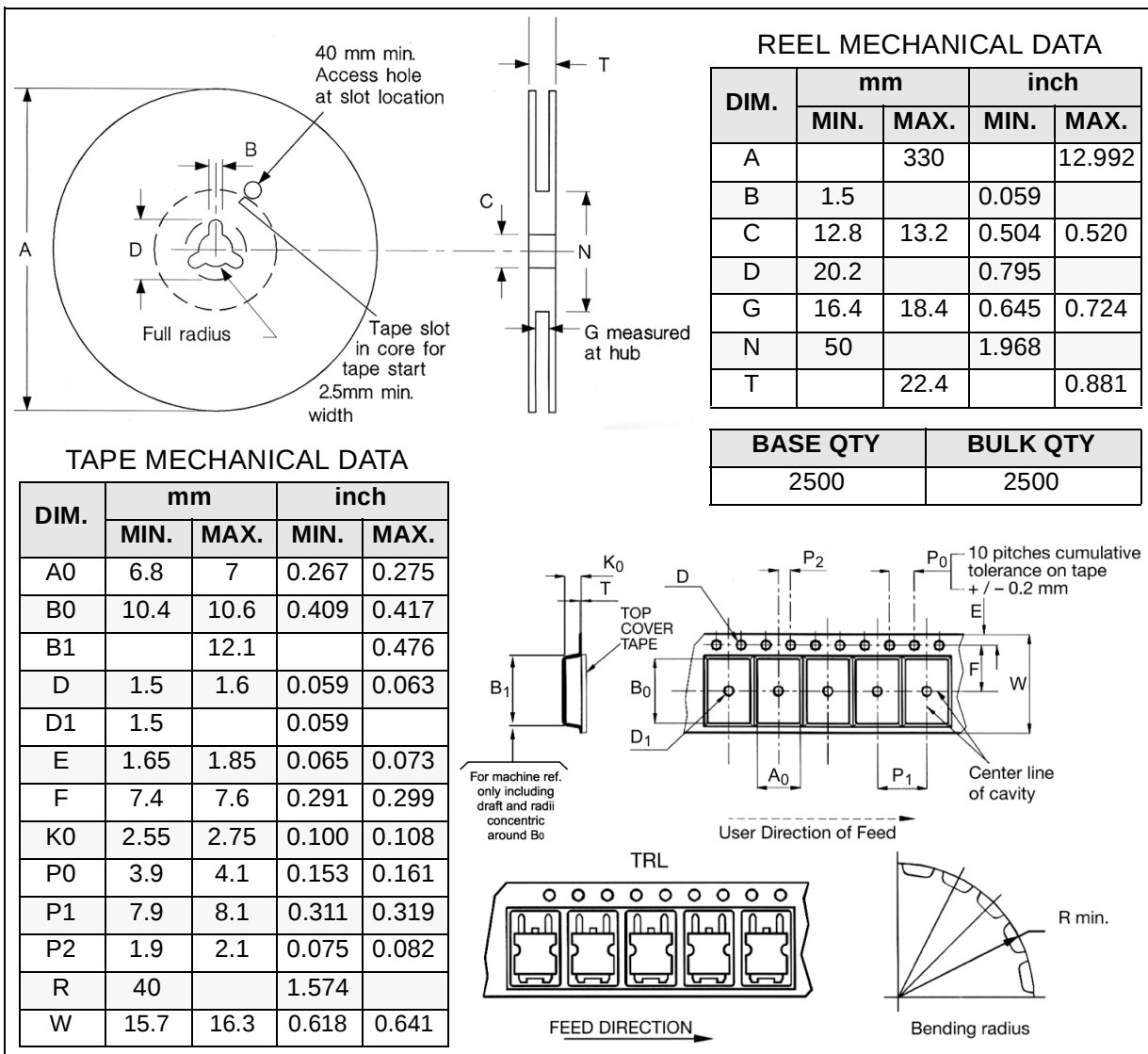
DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



* on sales type